Electronics

OPB815L, OPB815WZ Series

Features:

- Wide slot width: 0.375" (9.5 mm)
- Deep slot depth: 0.430" (10.9 mm)

Description:

The **OPB815** consists of an infrared Light Emitting Diode (LED) and an NPN silicon phototransistor mounted in a low-cost plastic housing. The device is designed to switch electrical states when an opaque object is passed through the slot. The slot is wider and deeper than many slotted switches and will accommodate a variety of different materials.

This device can be ordered with PCBoard solderable leads (OPB815L) or with 26 AWG stranded, UL rated wire length of 24" [610 mm] (OPB815WZ).

Custom electrical, wire and cabling and connectors are available. Contact your local representative or OPTEK for more information.

Ordering Information								
				Aperture	Lead			
OPB815L	890 nm	Transistor	0.375" / 0.430"	None	0.10" / 0.53"			
OPB815WZ	890 nm	Transistor	0.375"/ 0.430"	None	24" / 26 AWG			

Applications:

- Non-contact object sensing
- Assembly line automation
- Machine automation
- Equipment security
- Machine safety

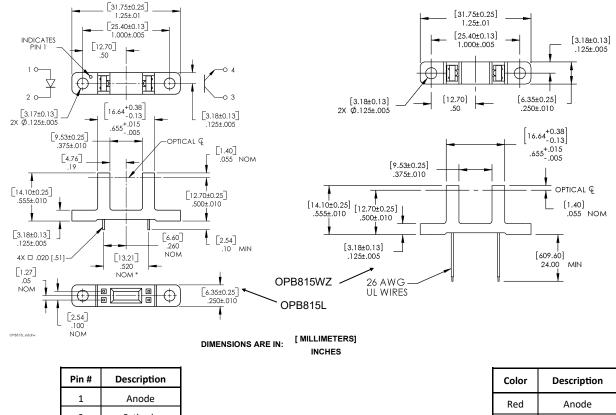


General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.



OPB815L, OPB815WZ Series



Description		
Anode		
Cathode		
Collector		
Emitter		

 Red
 Anode

 Black
 Cathode

 White
 Collector

 Green
 Emitter

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Electrical Specifications

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Storage & Operating Temperature Range	-40° C to +80° C
Lead Soldering Temperature [1/16 inch (1.6mm) from the case for 5 sec. with soldering iron]	260° C
Input Infrared LED	
Continuous Forward Current	50 mA
Reverse Voltage	2 V
Power Dissipation ⁽²⁾	100 mW
Output Phototransistor	
Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Power Dissipation ⁽²⁾	100 mW

Electrical Characteristics (T_A = 25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	ТҮР	ΜΑΧ	UNITS	TEST CONDITIONS			
Input Infrared LED (see OP240 for additional information)									
V _F	Forward Voltage		-	1.7	V	I _F = 20 mA			
I _R	Reverse Current		-	100	μΑ	V _R = 2 V			
Output Phototransistor (see OP550 for additional information)									
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	-	-	V	I _c =1 mA			
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5	-	-	v	I _E = 100 μA			
I _{CEO}	Collector-Emitter Dark Current	-	-	100	nA	$V_{CE} = 10 \text{ V}, I_F = 0, E_E = 0$			
Coupled									
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	-	-	0.4	V	I _C = 500 μA, I _F = 20 mA			
I _{C(ON)}	On-State Collector Current	3.5	-	16	mA	V _{CE} = 10 V, I _F = 20 mA			

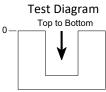
Notes:

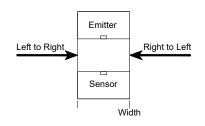
(1) All wires are 26 AWG stranded, UL rated.

(2) Derate linearly 1.67mW/°C above 25° C.

(3) Methanol or isopropanol are recommended as cleaning agents. The plastic housing is soluble in chlorinated hydrocarbons and keytones.

(4) All parameters tested using pulse techniques.





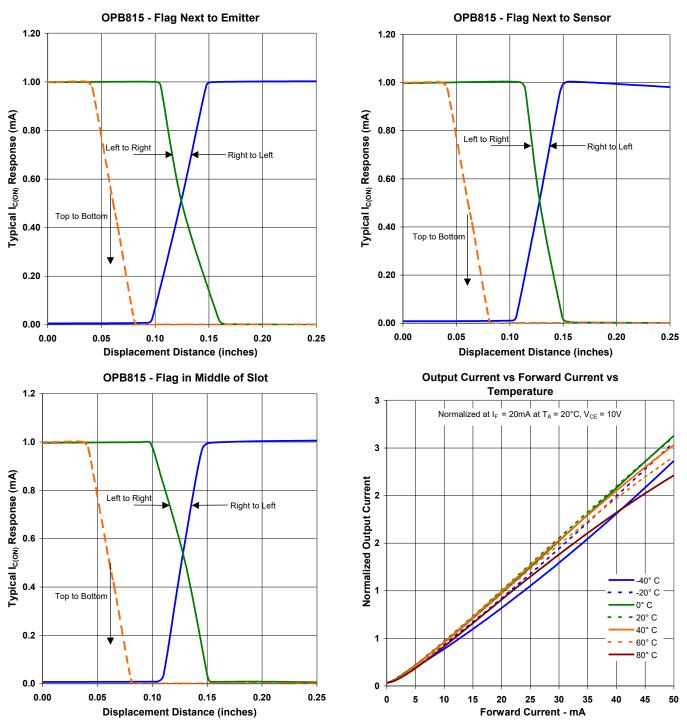
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Refer to Test Diagram on page 2 for definition of "Top to Bottom", "Left to Right" and "Right to Left"

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